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Sheet 1 of 1

**Complete if Known**

Application Number	09/945500
Filing Date	August 30, 2001
First Named Inventor	Forbes, Leonard
Group Art Unit	2818
Examiner Name	Pham, Ly

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**US PATENT DOCUMENTS**

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date if Appropriate
LP	US-6,210,999	04/03/2001	Gardner, , et al.	438	183	12/04/1998
LP	US-6,541,280	04/01/2003	Kaushik, , et al.			03/20/2001

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No *	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T*
LP		AARIK, JAAN , et al., "Anomalous effect of temperature on atomic layer deposition of titanium oxide", <u>Journal of Crystal Growth</u> , (2000),pp. 531-537	
LP		AARIK, JAAN , et al., "Texture development in nanocrystalline hafnium dioxide thin films grown by atomic layer deposition", <u>Journal of Crystal Growth</u> , (2000),pp. 105-113	
LP		FERGUSON, J D., et al., "Atomic layer deposition of Al <sub>2</sub> O <sub>3</sub> and SiO <sub>2</sub> on BN particles using sequential surface reaction", <u>Applied Surface Science</u> , (2000),pp. 280-292	
LP		KIM, YONG S., et al., "Effect of rapid thermal annealing on the structure and the electrical properties of atomic-layer-deposited Ta <sub>2</sub> O <sub>5</sub> films", <u>Journal of the Korean Physical Society</u> , (December 2000),pp. 975-979	
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LP		KUKLI, KAUPO , et al., "Atomic layer deposition of zirconium oxide from zirconium tetraiodide, water and hydrogen peroxide", <u>Journal of Crystal Growth</u> , (2001),pp. 262-272	
LP		KUKLI, KAUPO , et al., "Real-time monitoring in atomic layer deposition of TiO <sub>2</sub> from TiI <sub>4</sub> and H <sub>2</sub> O-H <sub>2</sub> O <sub>2</sub> ", <u>American Chemical Society</u> , (2000),pp. 8122-8128	
LP		LEE, J. , "Effect of Polysilicon Gate on the Flatband Voltage Shift and Mobility Degradation for ALD-Al <sub>2</sub> O <sub>3</sub> Gate Dielectric", <u>IEDM</u> , (2000),pp. 645-648	
LP		PARANJPE, AJIT , et al., "Atomic layer deposition of AlOx for thin film head gap application", <u>Journal of the Electrochemical Society</u> , (September 2001),pp. 465-471	
LP		SMITH, RYAN C., et al., "Chemical vapour deposition of the oxides of titanium, zirconium and hafnium for use as high-k materials in microelectronic devices. A carbon-free precursor for the synthesis of hafnium dioxide", <u>Advanced Materials for Optics and Electronics</u> , (2000),2 pages	

EXAMINER

DATE CONSIDERED

12/11/03

Substitute Disclosure Statement Form (PTO-1449)

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